# 2SB955(K)

## Silicon PNP Triple Diffused

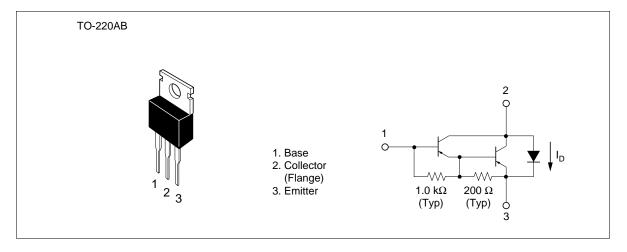
## **HITACHI**

ADE-208-863 (Z) 1st. Edition Sep. 2000

#### **Application**

Power switching complementary pair with 2SD1126(K)

#### **Outline**





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### **Absolute Maximum Ratings** (Ta = 25°C)

Item	Symbol	Rating	Unit
Collector to base voltage	$V_{\text{CBO}}$	-120	V
Collector to emitter voltage	V <sub>CEO</sub>	-120	V
Emitter to base voltage	$V_{EBO}$	<b>-7</b>	V
Collector current	I <sub>c</sub>	-10	A
Collector peak current	I <sub>C(peak)</sub>	<b>–</b> 15	A
C to E diode forward current	I <sub>D</sub> *1	10	A
Collector power dissipation	P <sub>c</sub> *²	50	W
Junction temperature	Tj	150	°C
Storage temperature	Tstg	-55 to +150	°C

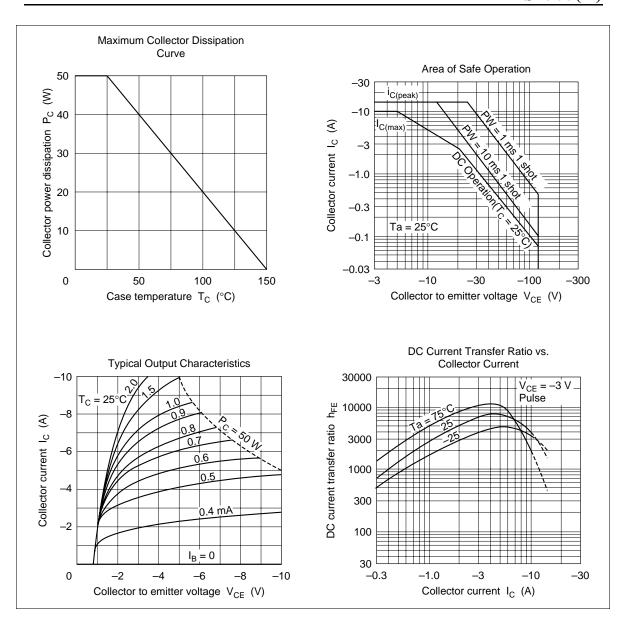
Notes: 1. Value at T<sub>C</sub> = 25°C

2.  $PW \le 1 \text{ ms } 1 \text{ shot}$ 

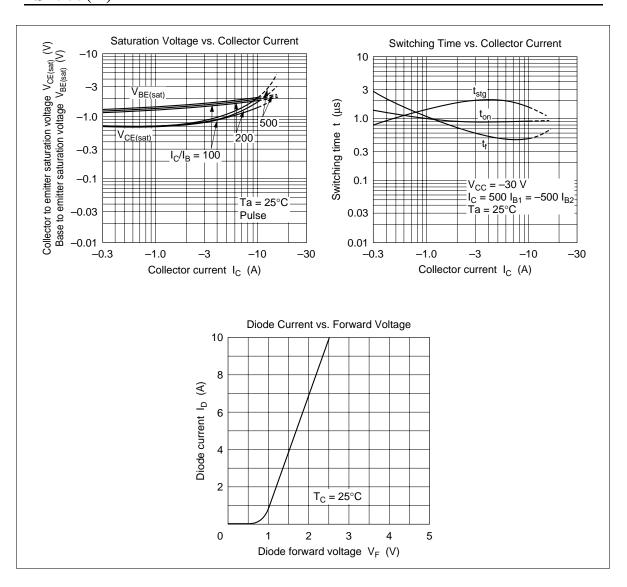
### **Electrical Characteristics** ( $Ta = 25^{\circ}C$ )

Item	Symbol	Min	Тур	Max	Unit	Test conditions
Collector to emitter breakdown voltage	$V_{(BR)CEO}$	-120	_	_	V	$I_{C} = -25 \text{ mA}, R_{BE} = \infty$
Emitter to base breakdown voltage	$V_{(BR)EBO}$	-7	_	_	V	$I_{\rm E} = -200 \text{ mA}, I_{\rm C} = 0$
Collector cutoff current	I <sub>CBO</sub>	_	_	-100	μΑ	$V_{CB} = -120 \text{ V}, I_{E} = 0$
	I <sub>CEO</sub>	_	_	-10	μΑ	V <sub>CE</sub> = −100 V, R <sub>BE</sub> = ∞
DC current transfer ratio	h <sub>FE</sub>	1000	_	20000		$V_{CE} = -3 \text{ V}, I_{C} = -5 \text{ A}^{*1}$
Collector to emitter saturation	V <sub>CE(sat)1</sub>	_	_	-1.5	V	$I_{\rm C} = -5 \text{ A}, I_{\rm B} = -10 \text{ mA}^{*1}$
voltage	V <sub>CE(sat)2</sub>	_	_	-3.0	V	$I_{\rm C} = -10 \text{ A}, I_{\rm B} = -0.1 \text{ A}^{*1}$
Base to emitter saturation	$V_{BE(sat)1}$	_	_	-2.0	V	$I_{\rm C} = -5 \text{ A}, I_{\rm B} = -10 \text{ mA}^{*1}$
voltage	V <sub>BE(sat)2</sub>	_	_	-3.5	V	$I_{\rm C} = -10 \text{ A}, I_{\rm B} = -0.1 \text{ A}^{*1}$
C to E diode forward voltage	$V_{D}$	_	_	3.0	V	I <sub>D</sub> = 10 A*1
Turn on time	t <sub>on</sub>	_	8.0	_	μs	V <sub>CC</sub> = -30 V
Turn off time	t <sub>off</sub>	_	4.0	_	μs	$I_{\rm C} = -5 \text{ A}, I_{\rm B1} = -I_{\rm B2} = -10 \text{ mA}$

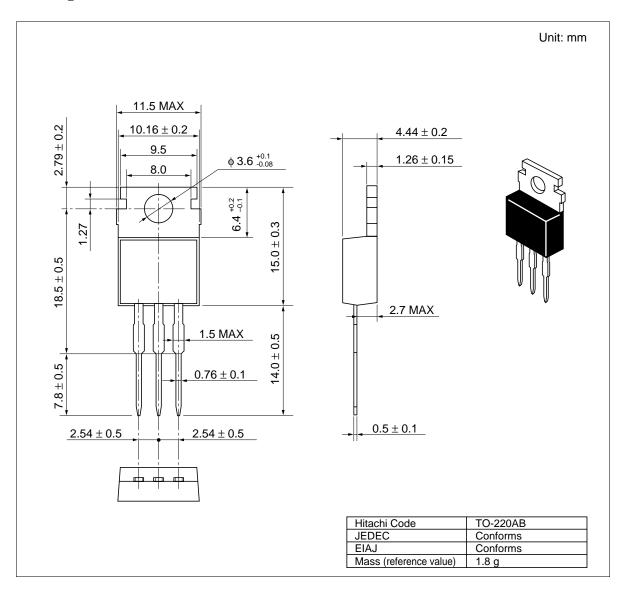
Note: 1. Pulse test



#### 2SB955(K)



### **Package Dimensions**



#### **Cautions**

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